

Key Features

- 20 ~ 3000 MHz, 50 Ohm impedance
- 1.3 dB noise figure
- 15 dB gain
- 1.35:1 VSWR
- 12 dBm P_{1dB}
- Precision machined housing
- RoHS compliant

Applications

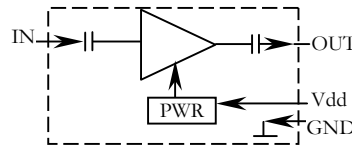
- LTE
- Receiver amplifiers
- RF bench tests
- Mobile base station applications



Absolute Maximum Ratings

Input CW RF Power	10 dBm
Maximum DC Voltage, V _{dd}	-0.5, +32 V
Operating Temperature	-40°C to +85°C
Storage Temperature	-40°C to +85°C

Functional Block Diagram



Ordering Information

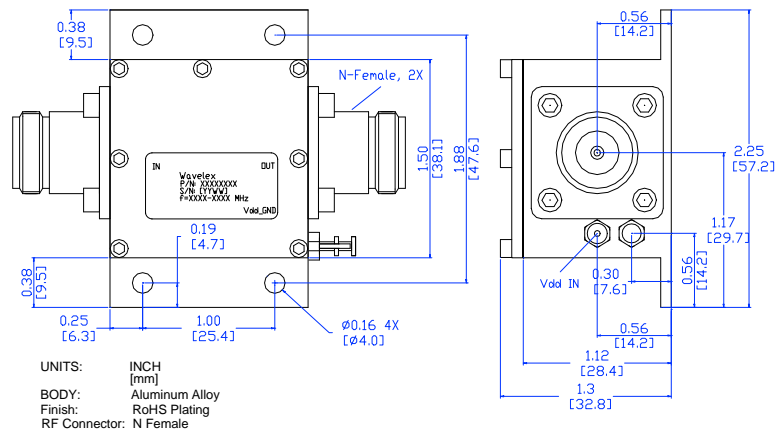
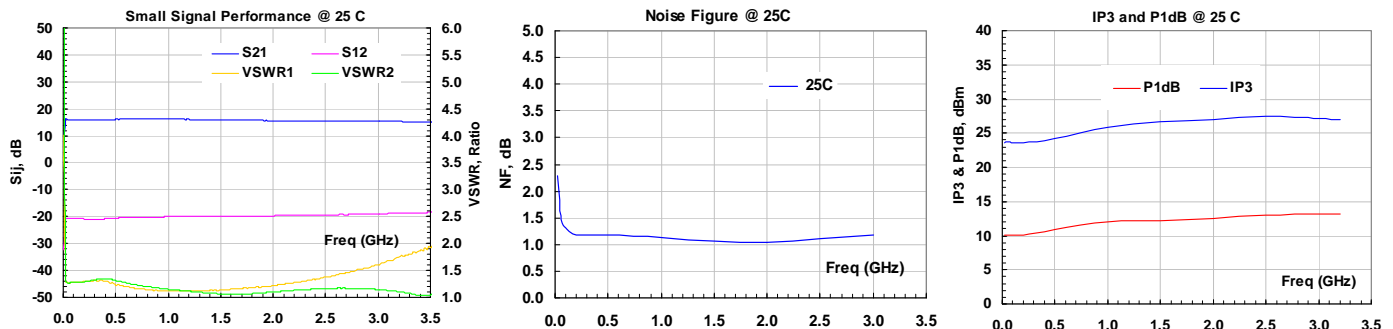
Model	Connectors
WLA0030N	N Female

Marking: WLA0030N

Specifications (Tested at +25°C)

tem	Symbol	Test Constraints	Min	Nom	Max	Unit
Frequency Range	BW	50 Ohm Impedance	20		3000	MHz
Gain	S ₂₁	20 – 3000 MHz	13	15	17	dB
Noise Figure	NF	20 – 3000 MHz		1.3	1.6	dB
VSWR	SWR _i	20 - 3000 MHz, all RF ports		1.35:1	1.8:1	Ratio
Gain Flatness	ΔG	20 – 3000 MHz		+/- 0.5		dB
Reverse Isolation	S ₁₂	20 – 3000 MHz	15	20		dB
Output Power 1dB Compression Point	P _{1dB}	20 – 3000 MHz	8	12		dBm
Output-Third-Order Interception point	IP ₃	Two-Tone, P _{out} = 0 dBm each, 1 MHz separation	20	25		dBm
Current Consumption	I _{dd}	V _{dd} = +12.0 V		25		mA
Power Supply Operating Voltage	V _{dd}		+8	+12	+16	V
Operating Temperature	T _o		-40		+85	°C
Thermal Resistance	R _{th,c}	Junction to case			215	°C/W

Typical Performance



Outline, IP-2